

*Concluded C1*  
second diffusion layer, the third diffusion layer being connected to the second diffusion layer, said third diffusion layer being fabricated at other than a bottom of said first diffusion layer, the first diffusion layer being circularly enclosed with the second and third diffusion layers.

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*area, region*  
21. (Amended) An input/output protection device for a semiconductor integrated circuit, said protection device comprising:

*\* C2*  
a substrate having a first conduction type;

a first region having a second conduction type opposite said first conduction type, said first region connected to an input/output terminal;

a second region enclosing said first region, said second region having said second conduction type, said first region and said second region being electrically separated;

a third region formed adjacent said second region, said third region having said second conduction type, said third region being formed below said second region at other than a bottom of said first region; and

a fourth region surrounded by said substrate and said first, second, and third regions, said fourth region having said first conduction type.

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#### REMARKS

Applicant wishes to thank Examiners Chaudhuri and Nguyen for the courteous and professional personal interview conducted on October 9, 2002. It is felt that this interview has been productive to clarify issues, thereby expediting prosecution.

Attached hereto is a marked up version of the changes made in the claims by the